

CSD17484F4 30-V N-Channel FemtoFET™ MOSFET

1 Features

- Low on-resistance
- Ultra-low Q_g and Q_{gd}
- Low-threshold voltage
- Ultra-small footprint (0402 Case Size)
 - 1.0 mm × 0.6 mm
- Ultra-low profile
 - 0.2-mm height
- Integrated ESD protection diode
 - Rated > 4-kV HBM
 - Rated > 2-kV CDM
- Lead and halogen free
- RoHS compliant

2 Applications

- Optimized for load switch applications
- Optimized for general purpose switching applications
- Battery applications
- Handheld and mobile applications

3 Description

This 99-m Ω , 30-V, N-Channel FemtoFET™ MOSFET is designed and optimized to minimize the footprint in many handheld and mobile applications. This technology is capable of replacing standard small signal MOSFETs while providing at least a 60% reduction in footprint size.

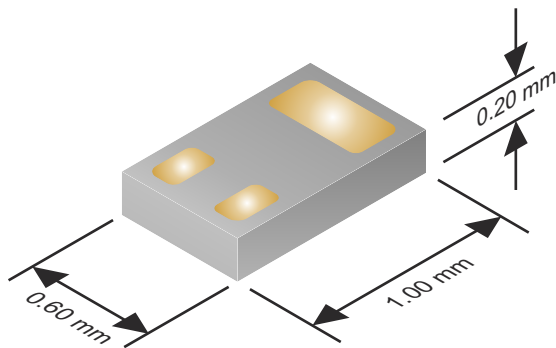


Figure 3-1. Typical Part Dimensions

Product Summary

$T_A = 25^\circ\text{C}$		TYPICAL VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	30	V
Q_g	Gate Charge Total (4.5 V)	920	pC
Q_{gd}	Gate Charge Gate-to-Drain	75	pC
$R_{DS(on)}$	Drain-to-Source On-Resistance	$V_{GS} = 1.8\text{ V}$	170
		$V_{GS} = 2.5\text{ V}$	125
		$V_{GS} = 4.5\text{ V}$	107
		$V_{GS} = 8.0\text{ V}$	99
$V_{GS(th)}$	Threshold Voltage	0.85	V

Device Information⁽¹⁾

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD17484F4	3000	7-Inch Reel	Femto (0402)	Tape and Reel
CSD17484F4T	250		1.00-mm × 0.60-mm Land Grid Array (LGA)	

- (1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	12	V
I_D	Continuous Drain Current ⁽¹⁾	3.0	A
I_{DM}	Pulsed Drain Current ^{(1) (2)}	18	A
I_G	Continuous Gate Clamp Current	35	mA
	Pulsed Gate Clamp Current ⁽²⁾	350	
P_D	Power Dissipation	500	mW
$V_{(ESD)}$	Human-Body Model (HBM)	4	kV
	Charged-Device Model (CDM)	2	
T_J, T_{stg}	Operating Junction, Storage Temperature	–55 to 150	$^\circ\text{C}$
E_{AS}	Avalanche Energy, Single Pulse $I_D = 7.1\text{ A}$, $L = 0.1\text{ mH}$, $R_G = 25\ \Omega$	2.5	mJ

- (1) Typical $R_{\theta JA} = 85^\circ\text{C/W}$ on 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu pad on a 0.06-in (1.52-mm) thick FR4 PCB.
- (2) Pulse duration $\leq 100\ \mu\text{s}$, duty cycle $\leq 1\%$.

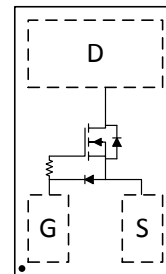


Figure 3-2. Top View



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4 Revision History

Changes from Revision C (December 2019) to Revision D (February 2022)	Page
• Added FemtoFET Surface Mount Guide note.....	9

Changes from Revision B (September 2017) to Revision C (December 2019)	Page
• Changed On-State Resistance vs Gate-to-Source Voltage by truncating V_{GS} from 20 V to 12 V.....	4

Changes from Revision A (August 2017) to Revision B (September 2017)	Page
• Deleted the <i>CSD68830F4 Embossed Carrier Tape Dimensions</i> section.....	9

Changes from Revision * (May 2015) to Revision A (August 2017)	Page
• Added the Section 6.1 and the Section 6 sections	7
• Updated the Section 7 section.....	8

5 Specifications

5.1 Electrical Characteristics

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-source voltage	$V_{GS} = 0\text{ V}, I_{DS} = 250\ \mu\text{A}$	30			V
I_{DSS}	Drain-to-source leakage current	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$			100	nA
I_{GSS}	Gate-to-source leakage current	$V_{DS} = 0\text{ V}, V_{GS} = 12\text{ V}$			50	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{DS} = 250\ \mu\text{A}$	0.65	0.85	1.10	V
$R_{DS(on)}$	Drain-to-source on-resistance	$V_{GS} = 1.8\text{ V}, I_{DS} = 0.5\text{ A}$		170	270	m Ω
		$V_{GS} = 2.5\text{ V}, I_{DS} = 0.5\text{ A}$		125	160	
		$V_{GS} = 4.5\text{ V}, I_{DS} = 0.5\text{ A}$		107	128	
		$V_{GS} = 8\text{ V}, I_{DS} = 0.5\text{ A}$		99	121	
g_{fs}	Transconductance	$V_{DS} = 15\text{ V}, I_{DS} = 0.5\text{ A}$		4		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 15\text{ V},$ $f = 1\text{ MHz}$		150	195	pF
C_{oss}	Output capacitance			44	57	pF
C_{riss}	Reverse transfer capacitance			2.2	2.9	pF
R_G	Series gate resistance			8		Ω
Q_g	Gate charge total (4.5 V)	$V_{DS} = 15\text{ V}, I_{DS} = 0.5\text{ A}$		920	1200	pC
Q_g	Gate charge total (8.0 V)			1570	2040	pC
Q_{gd}	Gate charge gate-to-drain			75		pC
Q_{gs}	Gate charge gate-to-source			280		pC
$Q_{g(th)}$	Gate charge at V_{th}			140		pC
Q_{oss}	Output charge		$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}$		1400	
$t_{d(on)}$	Turnon delay time	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V},$ $I_{DS} = 0.5\text{ A}, R_G = 2\ \Omega$		3		ns
t_r	Rise time			1		ns
$t_{d(off)}$	Turnoff delay time			11		ns
t_f	Fall time			4		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode forward voltage	$I_{SD} = 0.5\text{ A}, V_{GS} = 0\text{ V}$		0.73	0.9	V
Q_{rr}	Reverse recovery charge	$V_{DS} = 15\text{ V}, I_F = 0.5\text{ A}, di/dt = 300\text{ A}/\mu\text{s}$		1300		pC
t_{rr}	Reverse recovery time			6.2		ns

5.2 Thermal Information

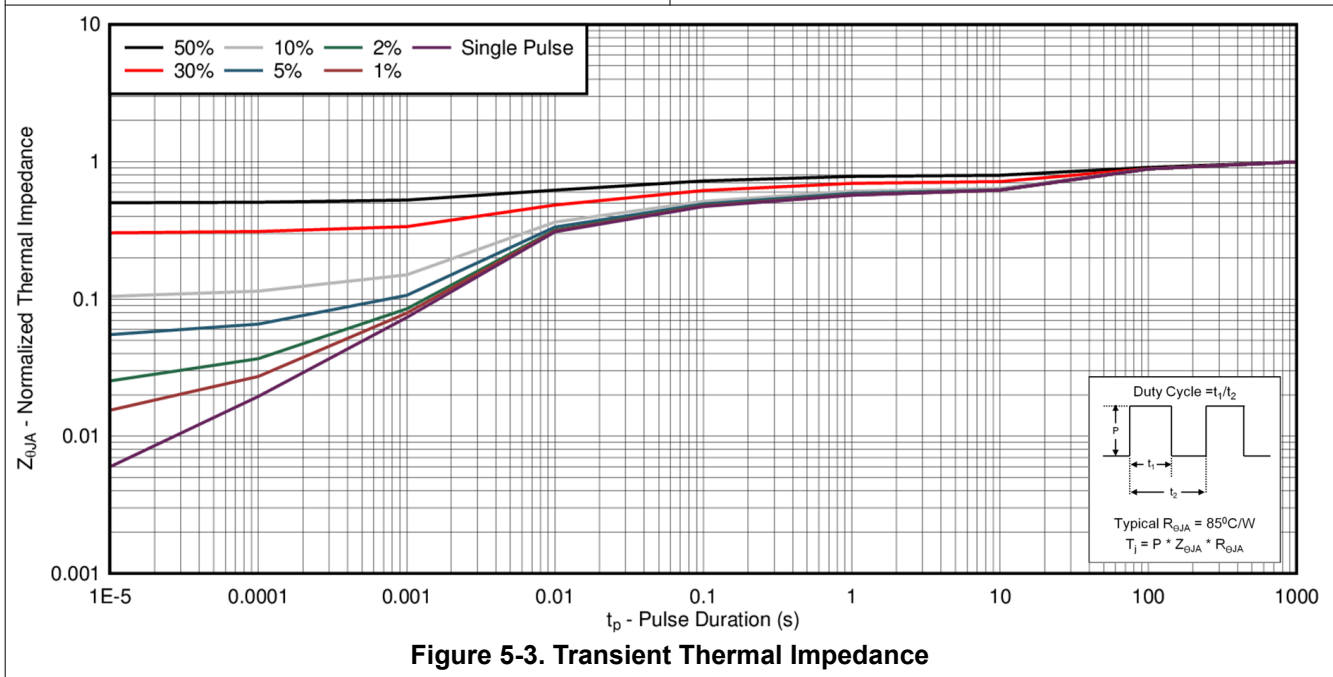
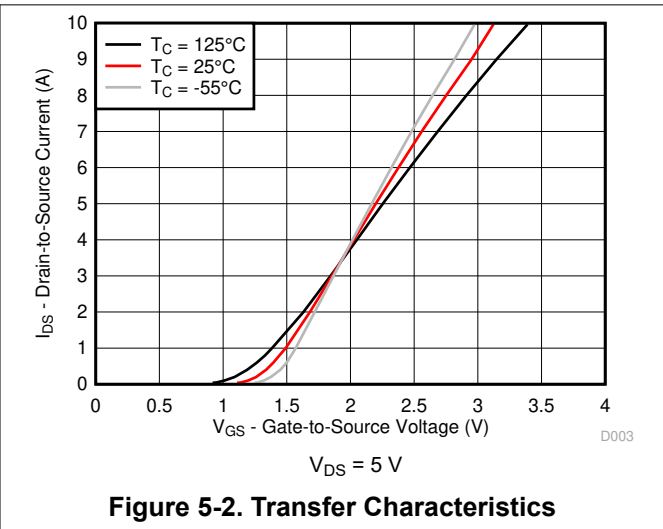
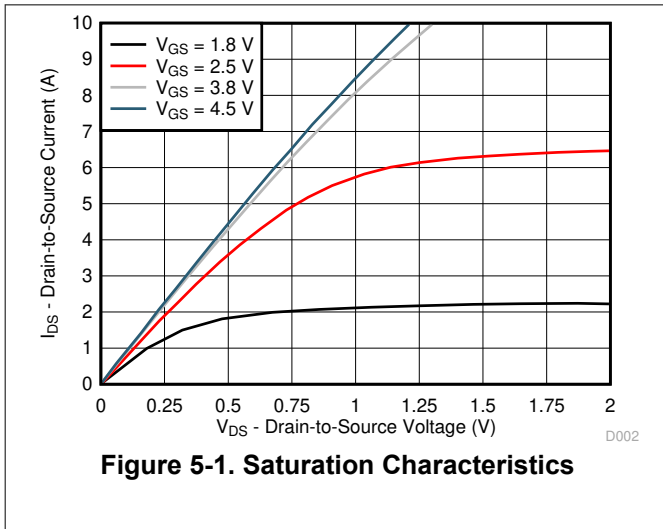
$T_A = 25^\circ\text{C}$ (unless otherwise stated)

THERMAL METRIC		TYPICAL VALUES	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾	85	$^\circ\text{C}/\text{W}$
	Junction-to-ambient thermal resistance ⁽²⁾	245	

- (1) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.
(2) Device mounted on FR4 material with minimum Cu mounting area.

5.3 Typical MOSFET Characteristics

$T_A = 25^\circ\text{C}$ (unless otherwise stated)



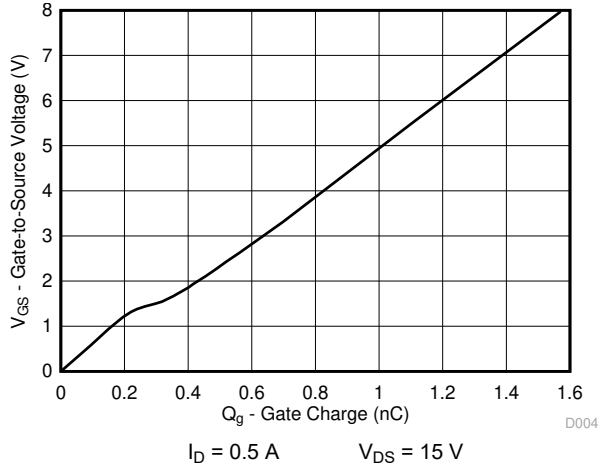


Figure 5-4. Gate Charge

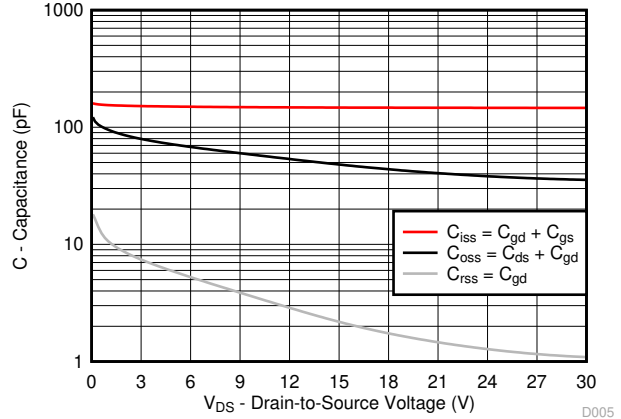


Figure 5-5. Capacitance

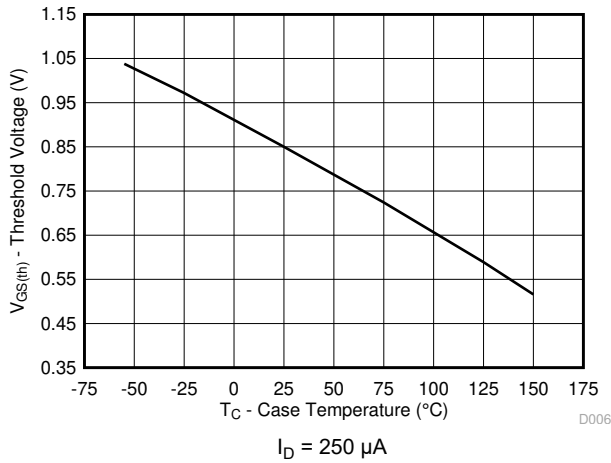


Figure 5-6. Threshold Voltage vs Temperature

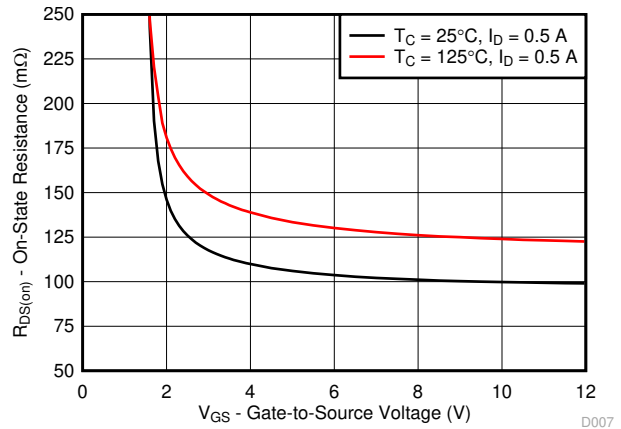


Figure 5-7. On-State Resistance vs Gate-to-Source Voltage

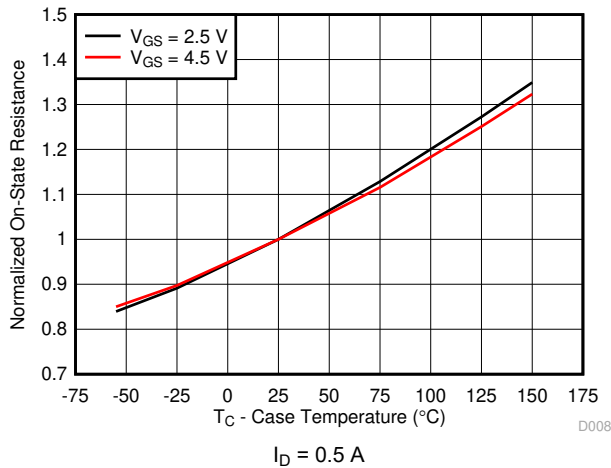


Figure 5-8. Normalized On-State Resistance vs Temperature

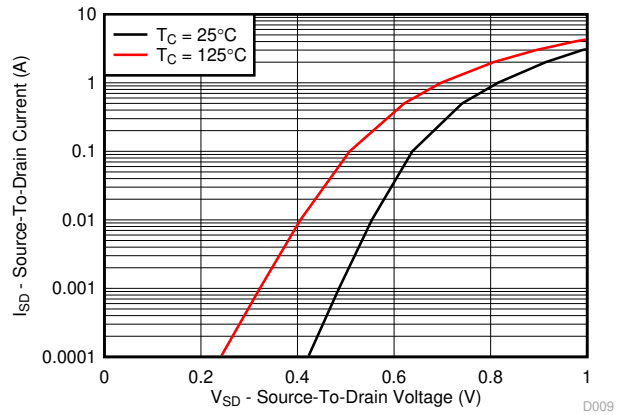


Figure 5-9. Typical Diode Forward Voltage

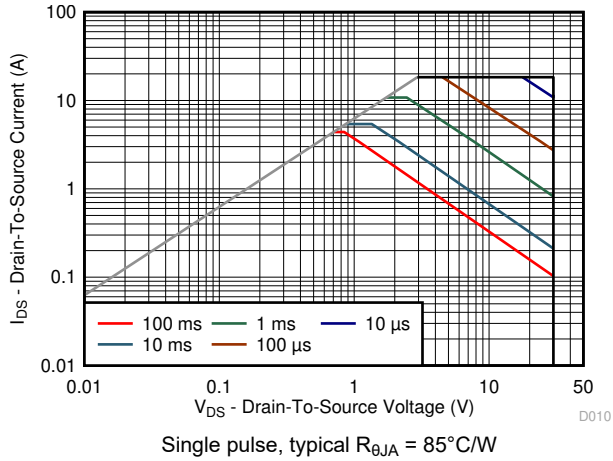


Figure 5-10. Maximum Safe Operating Area

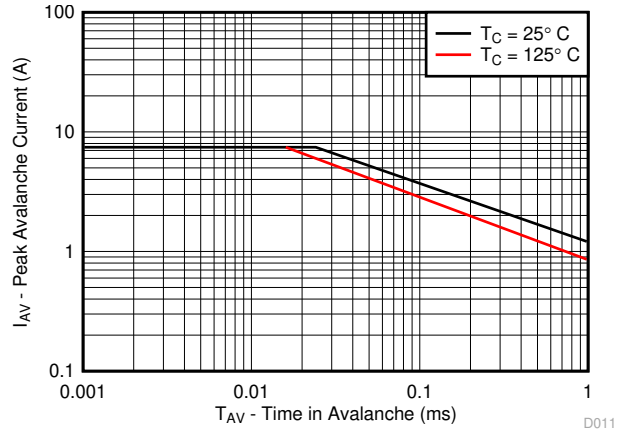


Figure 5-11. Single Pulse Unclamped Inductive Switching

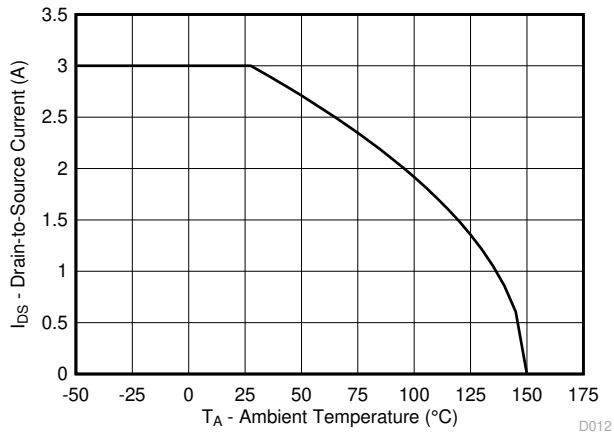


Figure 5-12. Maximum Drain Current vs Temperature

6 Device and Documentation Support

6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

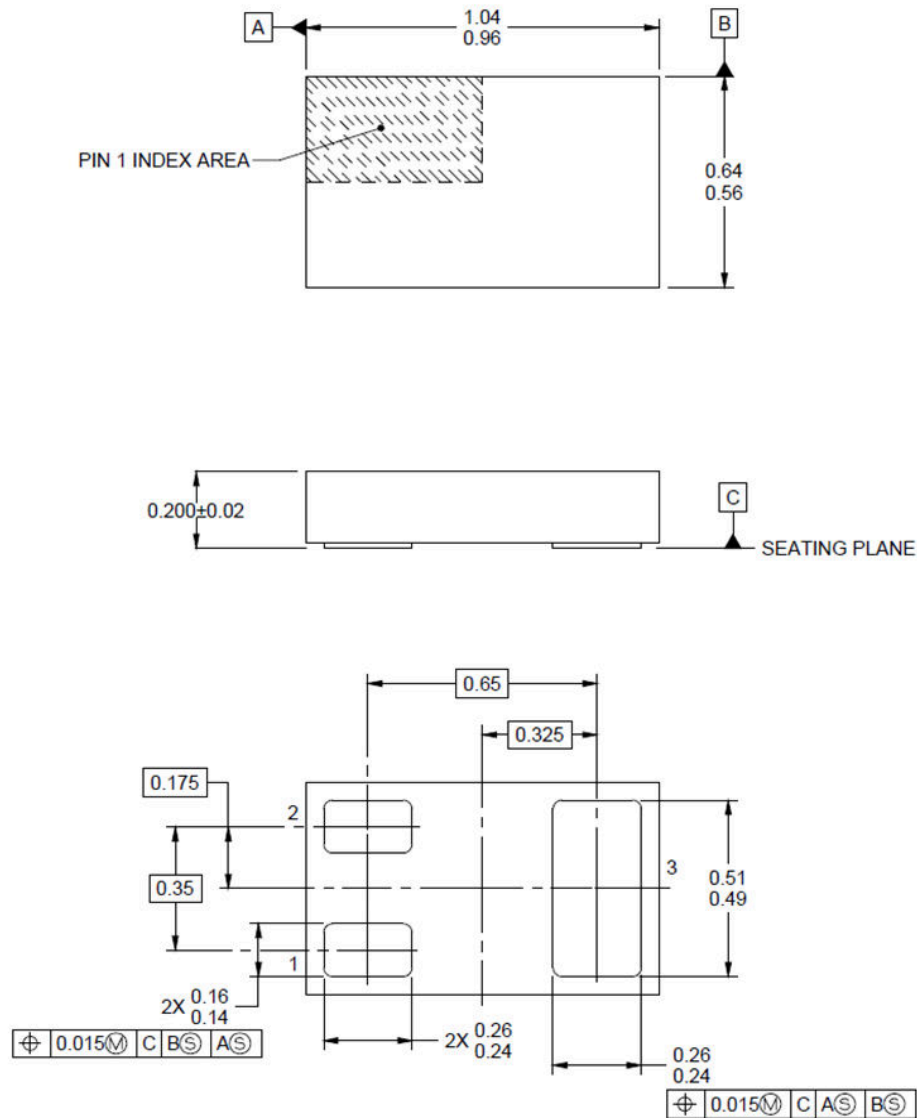
6.2 Trademarks

FemtoFET™ is a trademark of Texas Instruments.
All trademarks are the property of their respective owners.

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Mechanical Dimensions

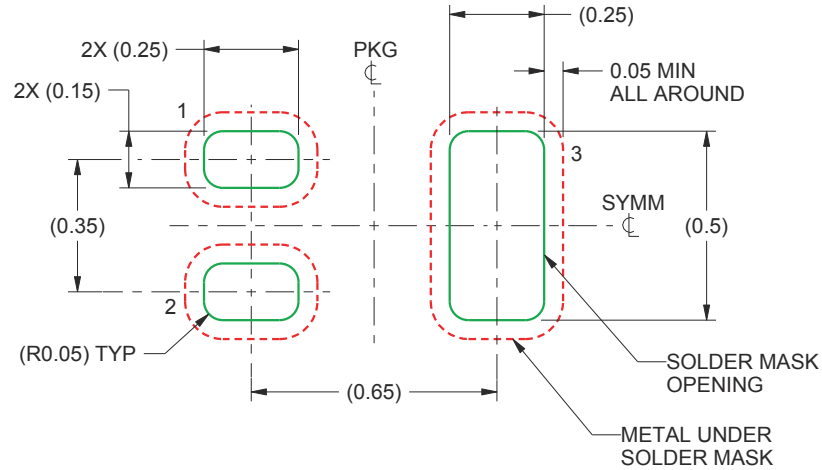


- A. All linear dimensions are in millimeters (dimensions and tolerancing per AME T14.5M-1994).
- B. This drawing is subject to change without notice.
- C. This package is a PB-free solder land design.

Table 7-1. Pin Configuration

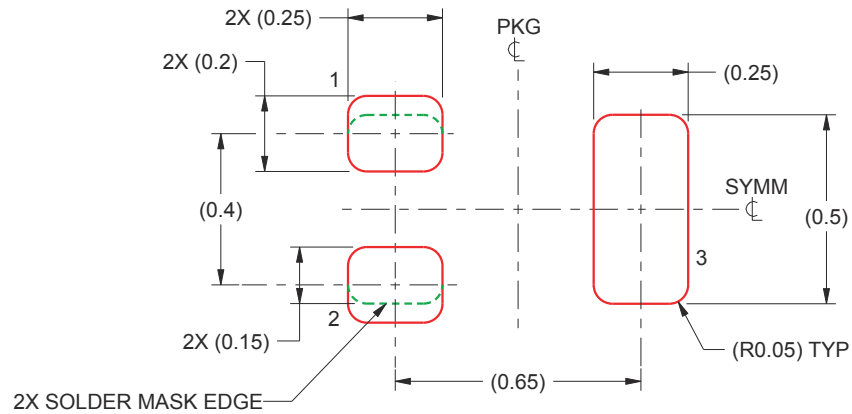
POSITION	DESIGNATION
Pin 1	Gate
Pin 2	Source
Pin 3	Drain

7.2 Recommended Minimum PCB Layout



- A. All dimensions are in millimeters.
- B. For more information, see [FemtoFET Surface Mount Guide \(SLRA003D\)](#).

7.3 Recommended Stencil Pattern



- A. All dimensions are in millimeters.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD17484F4	ACTIVE	PICOSTAR	YJJ	3	3000	RoHS & Green	NIAU	Level-1-260C-UNLIM	-55 to 150	G2	Samples
CSD17484F4T	ACTIVE	PICOSTAR	YJJ	3	250	RoHS & Green	NIAU	Level-1-260C-UNLIM	-55 to 150	G2	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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